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3 What is claimed is:

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5 1. A method of forming a semiconductor device comprising:

6 a) forming a gate structure over a substrate being doped with a first conductivity type  
7 impurity;

8 b) performing a doped depletion region implantation by implanting ions being the  
9 second conductive type to the substrate to form doped depletion regions  
10 beneath and separated from said source/drain regions;

11 c) performing a S/D implant by implanting ions having a second conductivity type  
12 into the substrate to form S/D regions adjacent to said gate;

13 (1) said doped depletion regions have an impurity concentration and thickness  
14 so that said doped depletion regions are depleted due to a built-in  
15 potential created between said doped depletion regions and said  
16 substrate.

17

18 2. The method of claim 1 wherein doped depletion region are not formed under said gate  
19 structure.

20 3. The method of claim 1 which further includes said doped depletion regions have a  
21 impurity concentration so that the built-in junction potential between said doped depletion  
22 regions and said substrate forms depletion regions in the substrate between the  
23 source/drain regions and the doped depletion region;

1                   said depletion regions have a net impurity concentration of the first  
2 conductivity type.

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4 4. The method of claim 1 which further includes said doped depletion regions have a  
5 impurity concentration so that the built-in junction potential between said doped depletion  
6 regions and said substrate forms depletion regions in the substrate between the  
7 source/drain regions and the doped depletion region;           said depletion regions have a  
8 net impurity concentration of the first conductivity type;  
9                   said depletion regions have a net impurity concentration between 1E16  
10 to 5E18 atom/cc.

11

12 5. The method of claim 1 which further includes implanting ions of a first impurity type  
13 into said substrate between said source/drain regions and said doped depletion regions.

14 6. The method of claim 1 which further includes performing an implant type selected from  
15 the group consisting of Halo implant, threshold voltage implant, and a field implant, that  
16 implant ions of a first impurity type into said substrate at least between said source/drain  
17 regions and said doped depletion regions.

18 7. The method of claim 1 wherein the region of said substrate between said source/drain  
19 regions and said doped depletion regions has a concentration of a first type impurity  
20 between 1E16 to 1E18 atom/cc;  
21 a channel region in said substrate under said gate structure; said channel region has a  
22 concentration of a second type impurity between 1E16 to 1E18 atom/cc.

23

- 1     8. The method of claim 1 wherein said depletion regions are fully depleted.
- 2     9. The method of claim 1 which further includes performing LDD implantation by  
3     implanting ions being a second type into the substrate using the gate structure as a mask to  
4     form LDD regions.
- 5     10. The method of claim 1 which further includes performing LDD implantation by  
6     implanting ions being a second type into the substrate using the gate structure as a mask to  
7     form LDD regions;
- 8                                the LDD regions are formed before the doped depletion regions.
- 9     11. The method of claim 1 which further includes performing LDD implantation by  
10    implanting ions being a second type into the substrate using the gate structure as a mask to  
11    form LDD regions;
- 12                                wherein the doped depletion regions are formed after the LDD regions.
- 13    12. The method of claim 1 wherein said first conductive type is p-type and said substrate  
14    has a boron concentration between  $1\text{E}17$  to  $1\text{E}19$  atom/cc.
- 15    13. The method of claim 1 wherein said first conductive type is n-type and said substrate  
16    100 has a As or P concentration between  $1\text{E}17$  to  $1\text{E}19$  atom/cc.
- 17    14. The method of claim 1 wherein said first conductive type substrate is comprised of Si  
18    or SiGe or strained Si, or relaxed SiGe or strained Ge.
- 19    15. The method of claim 1 wherein said gate structure has a channel width between 0.04  
20    and  $0.5\text{ }\mu\text{m}$ .

- 1 16. The method of claim 1 wherein the LDD implantation is performed by implanting As  
2 ions at a dose between  $5E14$  and  $1E16$  atoms / $cm^2$ , at an energy between 1keV and 10  
3 keV.
- 4 17. The method of claim 1 wherein the LDD implantation is performed by implanting  
5 Boron ions at a dose between  $1E14$  and  $5E15$  atoms / $cm^2$ , at an energy between 1 keV  
6 and 10 keV.
- 7 18. The method of claim 1 wherein the doped depletion region implantation is performed  
8 by implanting As or P ions at a dose between  $5E12$  and  $5E13$  atoms/ $cm^2$ , at an energy  
9 between 100 keV and 500 keV; said doped depletion region has a minimum depth below  
10 the substrate surface between 0.09 and 0.7  $\mu m$ .
- 11 19. The method of claim 1 wherein the doped depletion region implantation is performed  
12 by implanting boron ions at a dose between  $5E11$  and  $5E13$  atoms/ $cm^2$ , at an energy  
13 between 50 keV and 200 keV; said doped depletion region has a minimum depth below  
14 the substrate surface between 0.09 and 0.7  $\mu m$ .
- 15 20. The method of claim 1 wherein the S/D implant is performed by implanting arsenic  
16 (As) or phosphorus (P) ions at a dose between  $5E14$  to  $1E16$  atoms/ $cm^2$ , at an energy  
17 between 50 keV and 80 keV; said Source/drain regions have a depth below the substrate  
18 surface of between 0.04 and 0.5  $\mu m$ .
- 19 21. The method of claim 1 wherein said second conductivity type is p-type; and said S/D  
20 implant is performed by implanting boron ions at a dose between  $5E14$  to  $1E16$   
21 atoms/ $cm^2$ , at an energy between 50keV and 80keV; said source/drain regions have a depth  
22 below the substrate surface of between 0.04 and 0.5  $\mu m$ .
- 23 22. The method of claim 1 which further includes forming one or more spacers on the  
24 sidewalls of said gate structure.

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2 23. A method of forming a semiconductor device comprising:

3 a) forming a gate structure over on substrate being doped with a first conductivity

4 type impurity;

5 b) performing a doped depletion region implantation by implanting ions being the

6 second conductive type to the substrate to form doped depletion regions

7 beneath and separated from said source/drain regions;

8 (1) said doped depletion regions have an impurity concentration and thickness

9 so that said doped depletion regions are depleted due to a built-in

10 potential created between said doped depletion regions and said

11 substrate;

12 (2) said doped depletion regions have a impurity concentration so that the

13 built-in junction potential between said doped depletion regions

14 and said substrate forms depletion regions in the substrate between

15 the source/drain regions and the doped depletion region; said

16 depletion regions have a net impurity concentration of the first

17 conductivity type; said depletion regions have a net impurity

18 concentration between 1E16 to 1E18 atom/cc;

19 c) performing a S/D implant by implanting ions having a second conductivity type

20 into the substrate to form S/D regions adjacent to said gate;

21 (1) said substrate between said source/drain regions and said doped depletion

22 regions has a concentration of a first type impurity between 1E16 to

23 1E18 atom/cc.

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1 24. The method of claim 23 wherein doped depletion region are not formed under said  
2 gate structure.

3 25. The method of claim 23 wherein the region of said substrate between said source/drain  
4 regions and said doped depletion regions has a concentration of a first type impurity  
5 between 1E16 to 1E18 atom/cc;  
6 a channel region in said substrate under said gate structure; said channel region has a  
7 concentration of a second type impurity between 1E16 to 1E18 atom/cc.

8 26. The method of claim 23 which further includes forming one or more spacers on the  
9 sidewalls of said gate structure.

10 27. The method of claim 23 which further includes forming two or more spacers on the  
11 sidewalls of said gate structure prior to the doped depletion region implantation.

12

13 28. A semiconductor device comprising:

14 a semiconductor substrate having a surface; said semiconductor  
15 substrate being doped with a first conductivity type impurity; the top portion of said  
16 semiconductor substrate is comprised of a first doped layer of a first conductivity type;  
17 a gate structure over the surface of said semiconductor substrate; said  
18 gate structure comprising a gate dielectric layer and a gate electrode;  
19 source/drain regions in said semiconductor substrate to oppose each  
20 other with a channel region laterally residing therebetween at a location immediately  
21 beneath said gate structure,

1                   doped depletion regions of a second conductivity type in said a first  
2 doped layer of a first conductivity type under said source/drain regions;

3                   doped depletion regions are determined in impurity concentration and  
4 thickness to ensure that this layer is fully depleted due to a built-in potential creatable  
5 between said substrate and doped depletion regions;

6                   whereby said doped depletion regions reduce the capacitance between  
7 the source/drain regions and the substrate.

8 29. The semiconductor device of claim 28 which further includes said doped depletion  
9 regions under said source/drain regions, but not under said channel region.

10 30. The semiconductor device of claim 28 which further includes LDD regions that extend  
11 from said source/drain regions toward said channel region; said LDD regions being lower  
12 in impurity concentration and shallower in depth than said source/drain region.

13 31. The semiconductor device of claim 28 which further includes depletion regions and  
14 S/D depletion regions adjacent said doped depletion regions and between said  
15 source/drain regions: and

16                   said doped depletion regions and; said depletion regions have a net  
17 impurity concentration of the first conductivity type.

18 32. The semiconductor device of claim 28 which further includes depletion regions  
19 between said source/drain regions and said doped depletion regions; said depletion regions  
20 have a net impurity concentration of the first conductivity type; said depletion regions has  
21 a net impurity concentration between 1E16 to 1E18 atom/cc..

1 33. The semiconductor device of claim 28 which further includes said doped depletion  
2 regions have a impurity concentration so that the built-in junction potential between said  
3 doped depletion regions and said substrate forms depletion regions in the substrate  
4 between the source/drain regions and the doped depletion region;

5 said depletion regions have a net impurity concentration of the first  
6 conductivity type.

7 34. The semiconductor device of claim 28 which further includes said doped depletion  
8 regions have a impurity concentration so that the built-in junction potential between said  
9 doped depletion regions and said substrate forms depletion regions in the substrate  
10 between the source/drain regions and the doped depletion region; said depletion regions  
11 have a net impurity concentration of the first conductivity type;

12 said depletion regions have a net impurity concentration between 1E16  
13 to 1E18 atom/cc.

14 35. The semiconductor device of claim 28 which further includes one or more spacers on  
15 the sidewalls of said gate structure.